

L Number	Hits	Search Text	DB	Time stamp
-	2949	((438/638) or (438/637) or (438/627) or (438/702)).CCLS.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/28 10:05
-	247	((438/638) or (438/637) or (438/627) or (438/702)).CCLS.) and (silicon near carbide or SiC)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 14:26
-	2	(photoresist or (photo near resist)) same (poisoned or poisoning or poison) and (dual near damascene) and ((silicon near carbide) or SiC) with nitrogen)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 15:00
-	259	damascene and (SiCN or (silicon near carbide near nitride))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 15:01
-	0	damascene and ((SiCN or (silicon near carbide near nitride)) same barrier) and (poison with (photoresist or (photo near resist)))	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 15:03
-	117	damascene and ((SiCN or (silicon near carbide near nitride)) same barrier)	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/27 15:03
-	28	(dual near damascene) and (SiCN or "silicon carbide nitride") same (SiC or "silicon carbide")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/28 12:36
-	11	(barrier near layer) same (SiCN or "silicon carbide nitride") same (SiC or "silicon carbide")	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/28 12:54
-	197	maydan.in.	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/28 12:55
-	104	maydan.in. and semiconductor	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/28 12:55
-	69	(maydan.in. and semiconductor) and apparatus	USPAT; US-PGPUB; EPO; JPO; DERWENT; IBM TDB	2003/05/28 12:55